

600 V
Size 10
4" Wafer

Electrical Characteristics (Wafer Form)

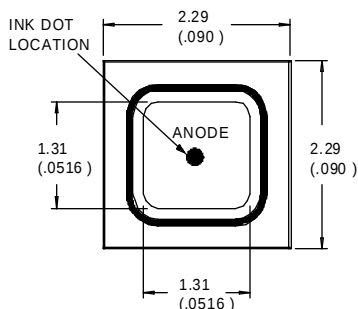
Parameter	Description	Guaranteed (Min/Max)	Test Conditions
V_{FM}	Forward Voltage	1.8V Max.	$T_J = 25^{\circ}C$, $I_F = 4A$
BV_R	Reverse Breakdown Voltage	600V Min.	$T_J = 25^{\circ}C$, $I_R = 250\mu A$
I_{RM}	Reverse Leakage Current	5 μA Max.	$T_J = 25^{\circ}C$, $V_R = 600V$

Mechanical Data

Normal Backmetal Composition, Thickness:	Cr-Ni-Ag (1 kA-4kA-6kA)
Normal Front Metal Composition, Thickness:	99% Al, 1% Si (3 microns)
Dimensions:	0.09" x 0.09"
Wafer Diameter:	100mm, with std. < 100 > flat
Wafer thickness:	.015" + / -.003"
Relevant Die Mechanical Dwg. Number	01-5159
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Ink Dot Location	See Die Outline drawing below
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : HFA08TB60

Die Outline



NOTES :

- ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES)
- CONTROLLING DIMENSION : (INCH)
- LETTER DESIGNATION :
S = SOURCE SK = SOURCE KELVIN
G = GATE IS = CURRENT SENSE
- DIMENSIONAL TOLERANCES
BONDING PADS : < 0.635 TOLERANCE = +/- 0.013
WIDTH < (.0250) TOLERANCE = +/- (.0005)
& > 0.635 TOLERANCE = +/- 0.025
LENGTH > (.0250) TOLERANCE = +/- (.0010)
OVERALL DIE < 1.270 TOLERANCE = +/- 0.102
WIDTH < (.050) TOLERANCE = +/- (.004)
& > 0.635 TOLERANCE = +/- 0.203
LENGTH > (.050) TOLERANCE = +/- (.008)
- UNLESS OTHERWISE NOTED ALL DIE ARE GEN III